

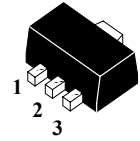
PNP EPITAXIAL PLANAR TRANSISTOR

(Pb) Lead(Pb)-Free

FEATURES

- * Low saturation voltage
- * Excellent DC current gain characteristics
- * Complements to 2SC4672

1. BASE
2. COLLECTOR
3. EMITTER



SOT-89

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Units
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current -Continuous	I _c	-2	A
Collector Power dissipation	P _C	500	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-50mA, I _E =0	-50	-	-	V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-50	-	-	V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-50mA, I _C =0	-6	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0	-	-	-0.1	mA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0	-	-	-0.1	mA
DC current gain	h _{FE}	V _{CE} =-2V, I _C =-500mA	82	-	270	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1A, I _B =-50mA	-	-	-0.35	V
Transition frequency	f _T	V _{CE} =-2V, I _C =-0.5A, f=100MHz	-	200	-	MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz	-	36	-	pF

CLASSIFICATION OF h_{FE}

Rank	P	Q
Range	82-180	120-270
Marking	AGP	AGQ

Typical Characteristics

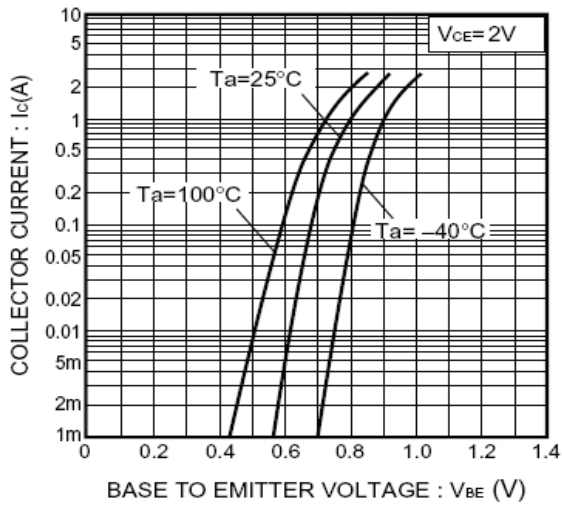


Fig.1 Grounded emitter propagation characteristics

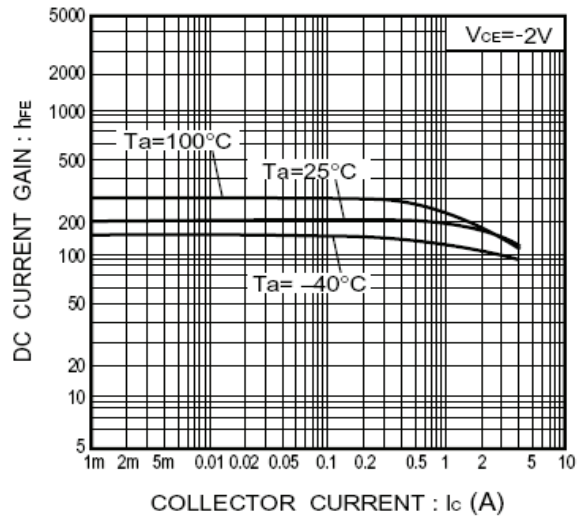


Fig.2 DC current gain vs. collector current

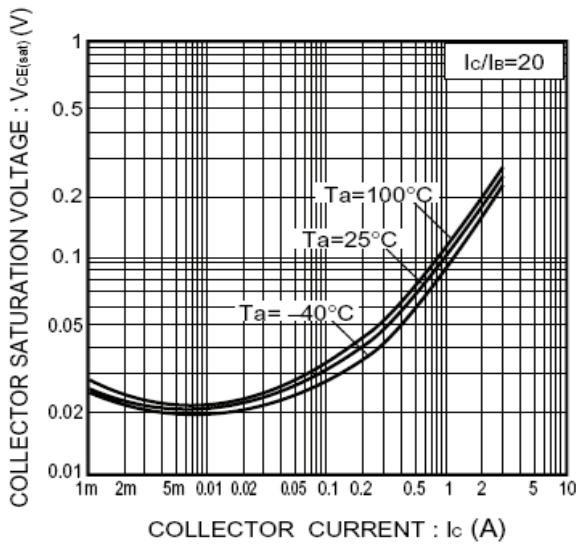


Fig.3 Collector-emitter saturation voltage vs. collector current

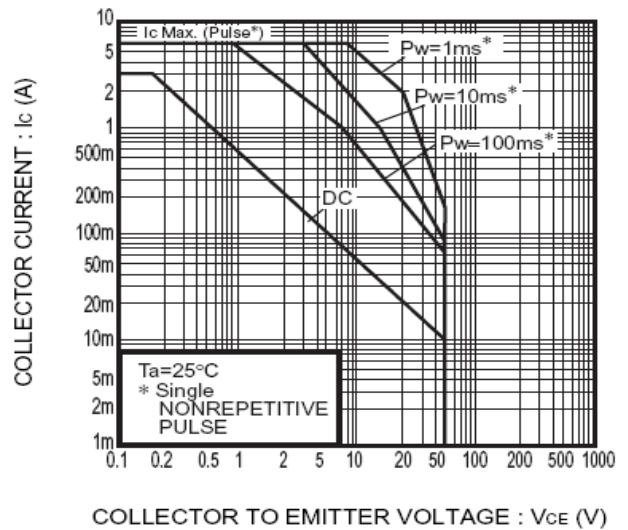
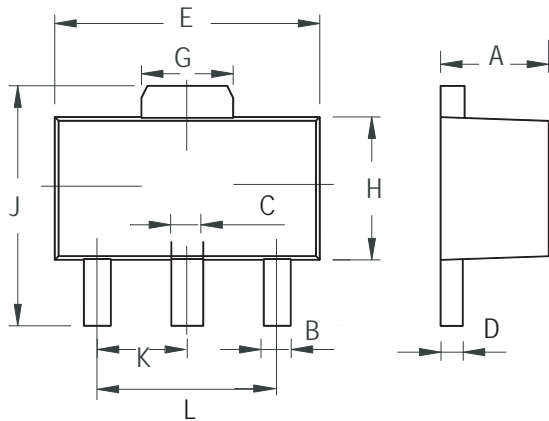


Fig.4 Safe Operating area

SOT-89 Outline Dimensions

unit:mm



SOT-89		
Dim	Min	Max
A	1.400	1.600
B	0.320	0.520
C	0.360	0.560
D	0.350	0.440
E	4.400	4.600
G	1.400	1.800
H	2.300	2.600
J	3.940	4.250
K	1.500TYP	
L	2.900	3.100